

ABSTRACT OF THE DISCLOSURE

The first present invention provides a nitride based
5 semiconductor photo-luminescent device having an active layer having a
quantum well structure, the active layer having both at least a high
dislocation density region and at least a low dislocation density region
lower in dislocation density than the high dislocation density region,
wherein the low dislocation density region includes a current injection
10 region into which a current is injected, and the active layer is less than $1 \times$
 10^{18} m^{-3} in impurity concentration.